

## N THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Ma. et al.

Serial No.: 10/784,904

Confirmation No.: 6141

Filed:

February 23, 2004

For:

Gate Electrode Dopant

Activation Method For Semiconductor

Manufacturing

MAIL STOP AMENDMENT Commissioner for Patents P.O. Box 1450

Alexandria, VA 22313-1450

§  $\omega$ 

Group Art Unit: 2812

Examiner:

Unknown

CERTIFICATE OF MAILING 37 CFR 1.8

I hereby certify that this correspondence is being deposited on April  $\mathcal{L}\mathcal{L}$  , 2005 with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450.

Date

Dear Sir:

## SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

The Applicants, and the Attorney who signs below on the basis of the information supplied by the inventor and the information in his file, submit herewith patents, publications, or other information of which they are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 CFR § 1.56.

While the information submitted in this Supplemental Information Disclosure Statement may be material pursuant to 37 CFR § 1.56, it is not intended to constitute an admission that any patent, publication, or other information referred to therein is prior art for this invention unless specifically designated as such.

In accordance with 37 CFR § 1.97, this Supplemental Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possibly material information as defined under 37 CFR § 1.56(a) exists.

The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

If the sum of \$180.00 is due under 37 CFR § 1.17(p) pursuant to § 1.97, the Commissioner is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to the Deposit Account No. 20-0782/AMAT/8830/KMT.

Respectfully submitted,

Keith M. Tackett

Registration No. 32,008

MOSER, PATTERSON & SHERIDAN, L.L.P.

3040 Post Oak Blvd. Suite 1500

Houston, TX 77056

Telephone: (713) 623-4844 Facsimile: (713) 623-4846 Attorney for Applicant(s)

Approved for use through 07/31/2006. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE ollection of information unless it displays a valid OMB control num

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT

sign (+) inside this box

form 1449A/PTO

5 2005

10/784,904 Application Number Filing Date February 23, 2004 First Named Inventor Ma, et al. Group Art Unit 2812 **Examiner Name** Unknown Attorney Docket Number AMAT/8830/FEP/PCVD/PJS

(Use as many sheets as necessary)

Sheet Submission Date April 22, 2005

	U.S. PATENT DOCUMENTS							
Examiner Initials*	Cite No.1	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear			
		Number-Kind Code <sup>2 (if known)</sup>						
	A1	US-6451119 B2	09/17/2002	SNEH, ET AL.				
	A2	US-6335280 B1	01/01/2002	VAN DER JEUGD				
	А3	US-6291319 B1	09/18/2001	YU, ET AL.				
	A4	US-20050079691 A1	04/14/2005	KIM, ET AL.				
	A5	US-20030189208 A1	10/09/2003	LAW, ET AL.				
	A6	US-20020145168 A1	10/10/2002	BOJARCZUK, JR., ET AL.				
	A7							

FOREIGN PATENT DOCUMENTS										
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document  Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T€				
	B1									

	NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T²				
	C1	International Search Report mailed February 22, 2005 for PCT/US2004/030872 (AMAT/8539-PCT)					
	C2	Kamins, et al. "Kinetics of selective epitaxial deposition of Si <sub>1.4</sub> Ge,", Applied Physics Letters, American Institute pf Physics. New York, US, vol. 61, no. 6, 10 August 1992, pp. 669-671					
	СЗ	Menon, et al. "Loading effect in SiGe layers grown by dichlorosilane- and silane-based epitaxy", Journal of Applied Physics, American Institute of Physics. New York, US, vol. 90, no. 9, 1 November 2001, pp. 4805-4809					
	C4	Sedgwick, et al. "Selective SiGe and heavily As doped Si deposited at low temperature by atmospheric pressure chemical vapor deposition", Journal of Vacuum Science and Technology: Part B, American Institute of Physics. New York, US, vol. 11, no. 3, 1 May 1993, pp. 1124-1128					
	C5	Uchino, et al. "A Raised Source/Drain Technology Using In-situ P-doped SiGe and B-doped Si for 0.1 µm CMOS ULSIs", Electron Devices Meeting, 1997. Technical Digest, International Washington, DC, USA 7-10 Dec. 1991, New York, NY, USA, IEEE, US, 7 December 1997, pp. 479-482					

Examiner **Date Considered** 

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered, Include popy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional), 2 See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document, skind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible, a Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1,97 and 1,98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450, DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450. If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.